

# High Voltage XPT™ IGBT

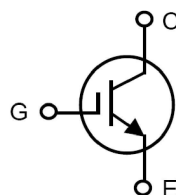
## IXYX40N250CHV

$$V_{CES} = 2500V$$

$$I_{C110} = 40A$$

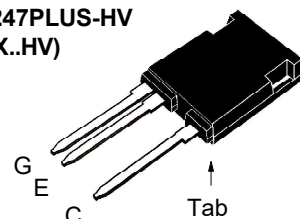
$$V_{CE(sat)} \leq 4.0V$$

$$t_{fi(typ)} = 134ns$$



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	2500	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	2500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	154	A
$I_{C110}$	$T_C = 110^\circ C$	40	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	370	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 80$ 1500	A V
$P_C$	$T_C = 25^\circ C$	1500	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
$F_C$	Mounting Force	20..120/4.5..27	N/lb
<b>Weight</b>		6	g

### TO-247PLUS-HV (IXYX..HV)



G = Gate  
C = Collector

E = Emitter  
Tab = Collector

### Features

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- UPS
- Motor Drives
- SMPS
- PFC Circuits
- High Frequency Power Inverters

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			15 $\mu A$ 4 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 40A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		3.2 4.4	V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 40\text{A}, V_{CE} = 10\text{V}$ , Note 1	24	42	S
$R_{Gi}$	Gate Input Resistance		2.0	$\Omega$
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		5470	pF
$C_{oes}$			204	pF
$C_{res}$			74	pF
$Q_{g(on)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		270	nC
$Q_{ge}$			28	nC
$Q_{gc}$			110	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		21	ns
$t_{ri}$			22	ns
$E_{on}$			11.7	mJ
$t_{d(off)}$			200	ns
$t_{fi}$			134	ns
$E_{off}$			6.9	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		21	ns
$t_{ri}$			22	ns
$E_{on}$			14.7	mJ
$t_{d(off)}$			255	ns
$t_{fi}$			250	ns
$E_{off}$			11.5	mJ
$R_{thJC}$			0.10	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

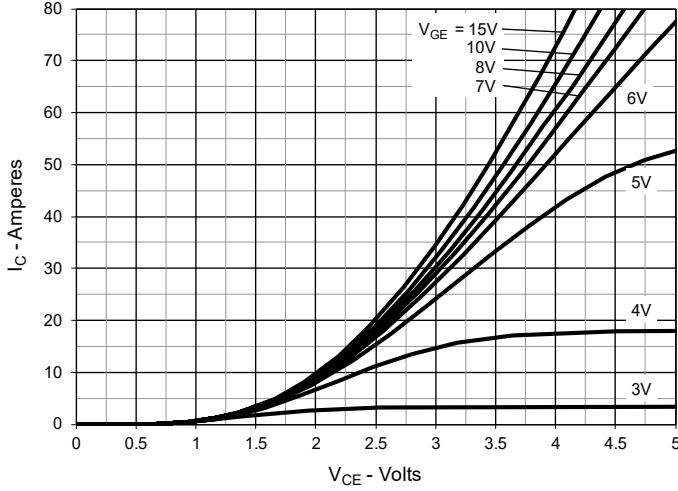
**Notes:**

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (Clamp),  $T_J$  or  $R_G$ .

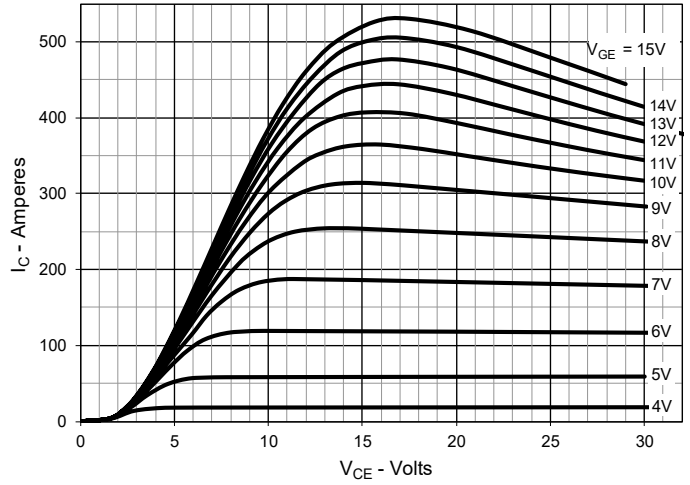
Littelfuse reserves the right to change limits, test conditions, and dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

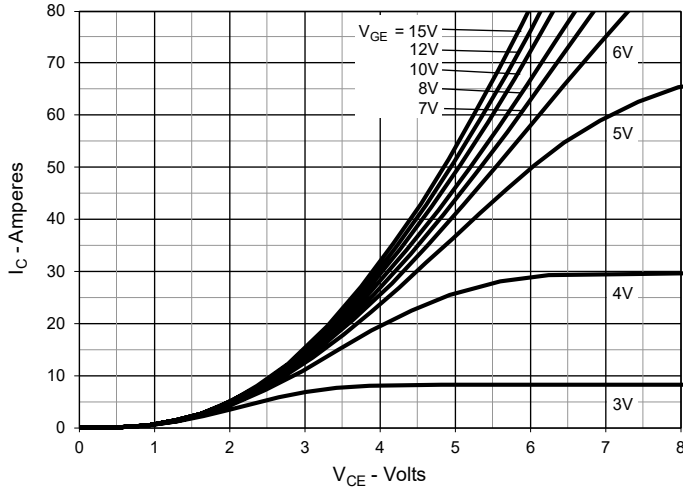
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



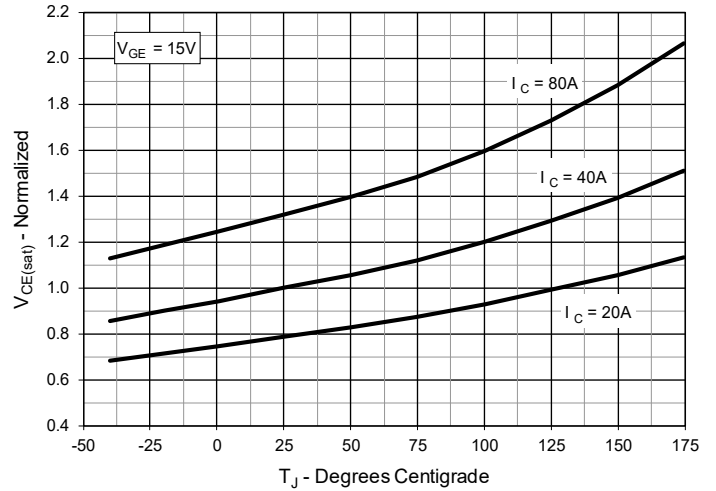
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



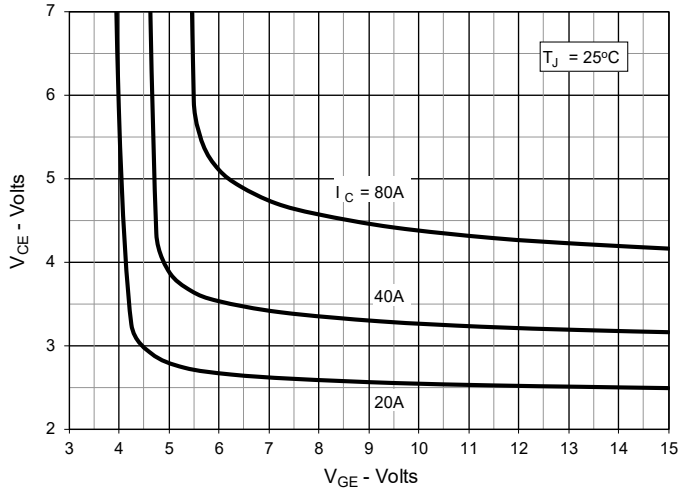
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



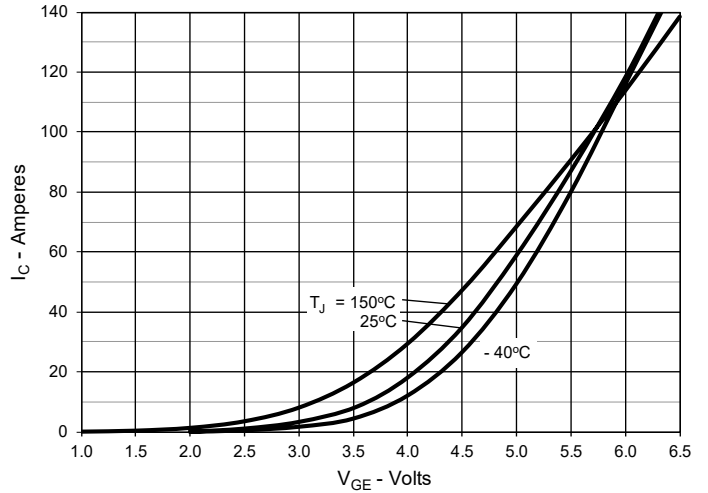
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



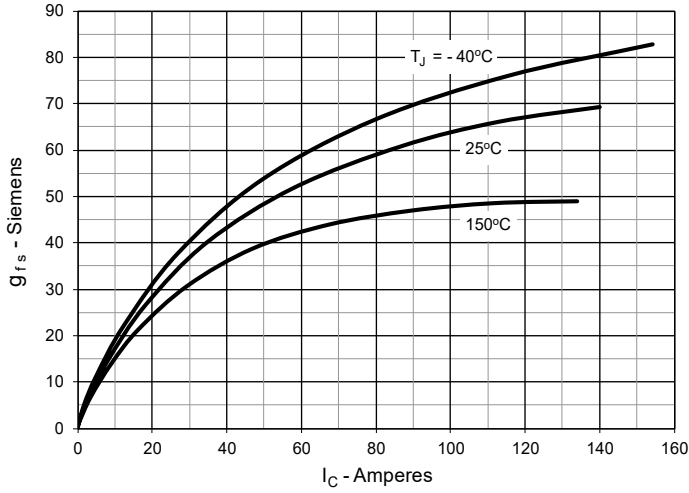
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



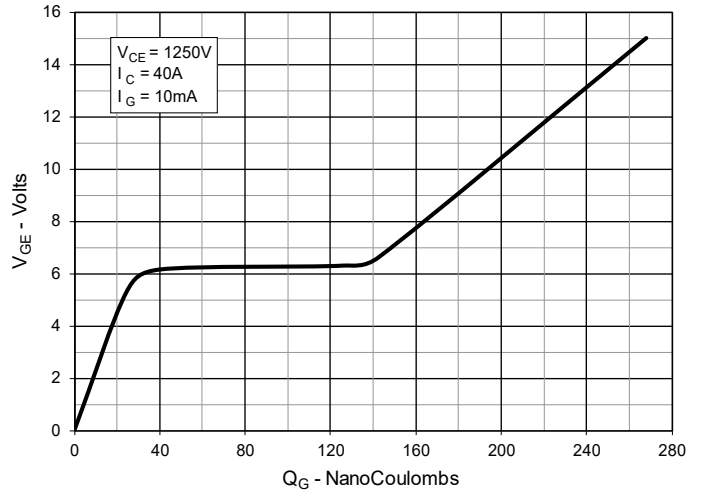
**Fig. 6. Input Admittance**



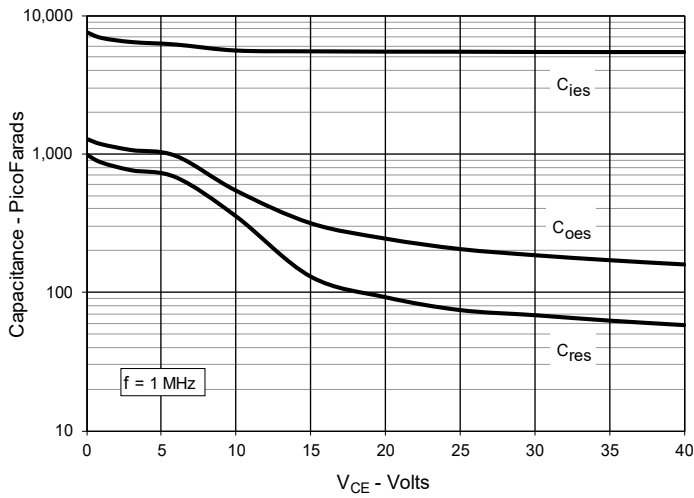
**Fig. 7. Transconductance**



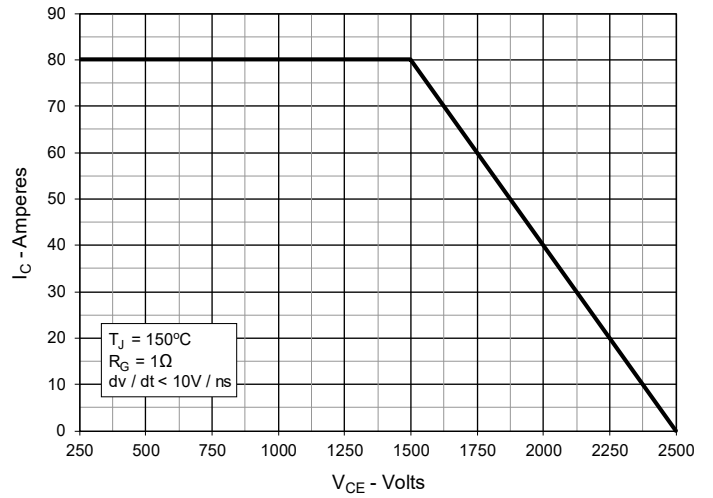
**Fig. 8. Gate Charge**



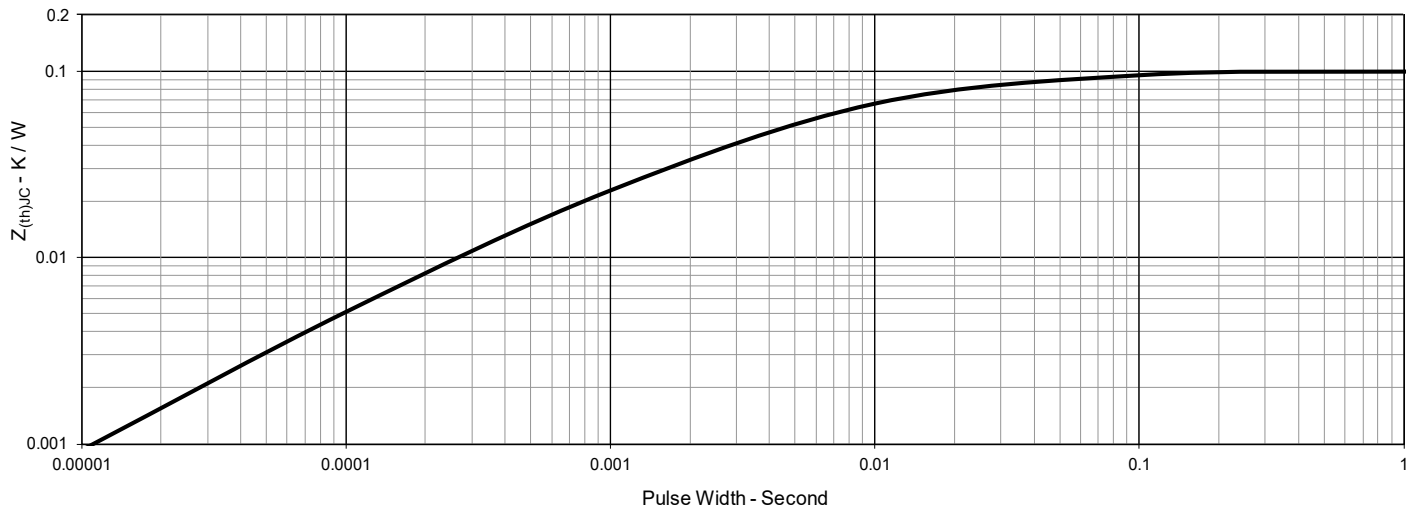
**Fig. 9. Capacitance**



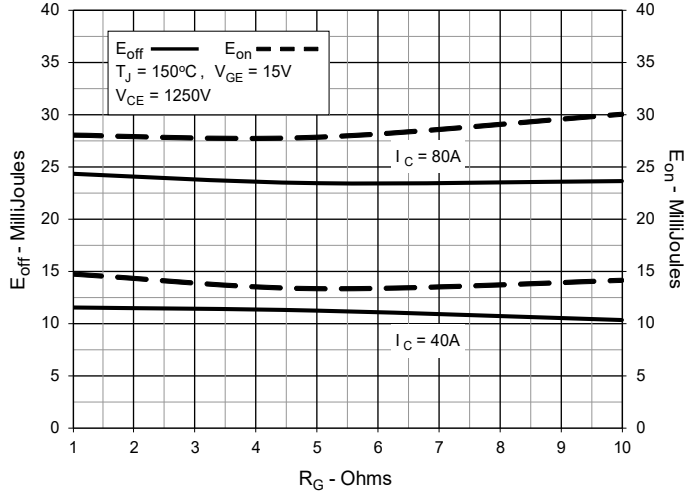
**Fig. 10. Reverse-Bias Safe Operating Area**



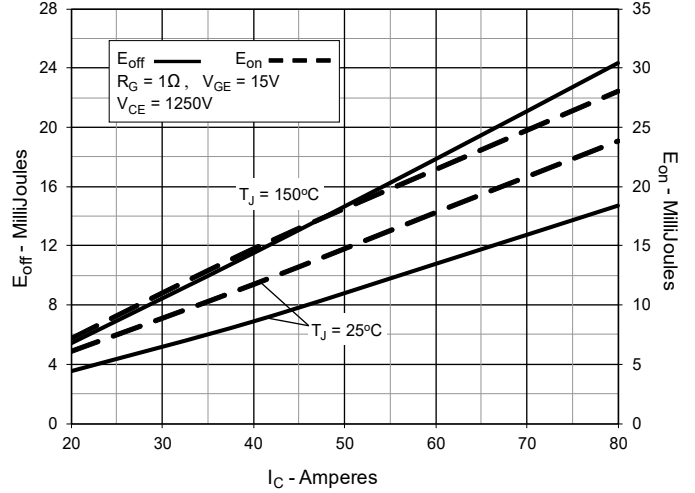
**Fig. 11. Maximum Transient Thermal Impedance**



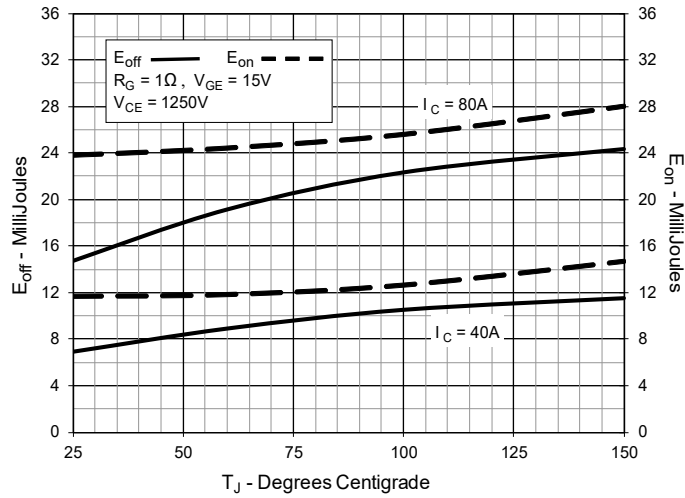
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



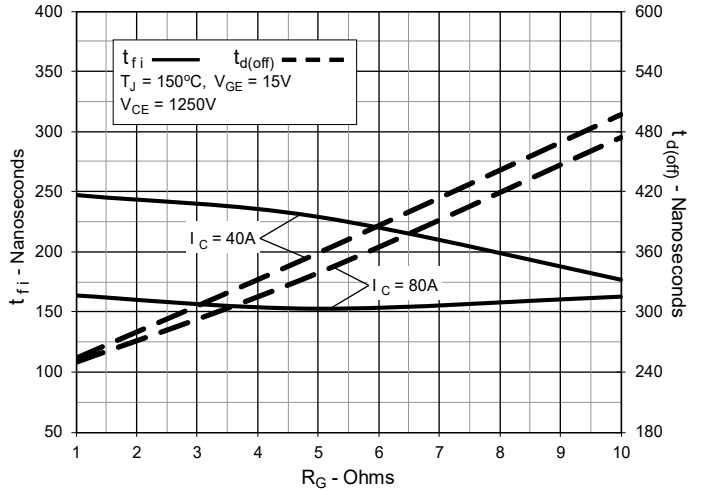
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



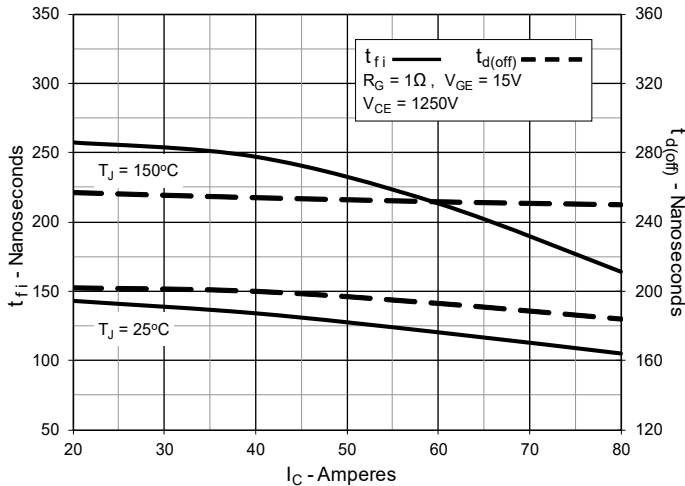
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



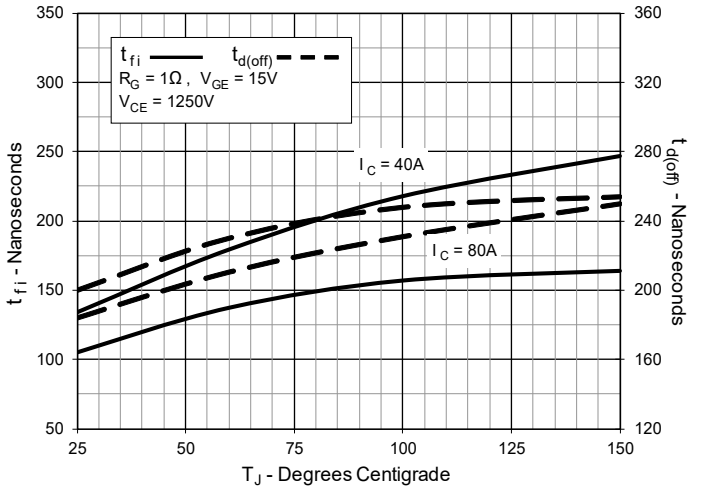
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



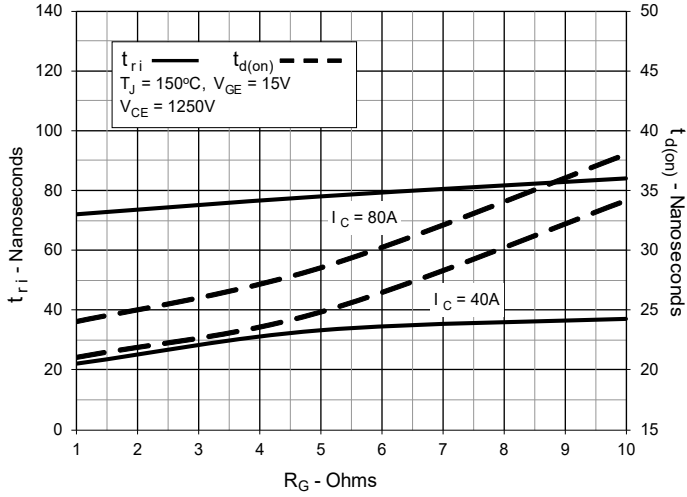
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



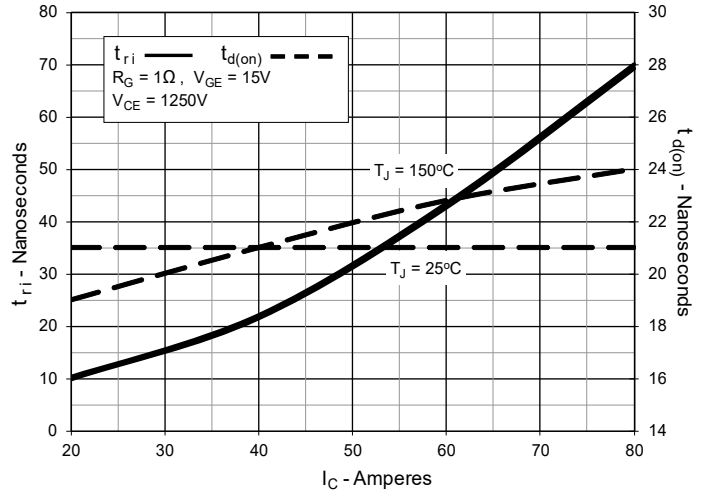
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



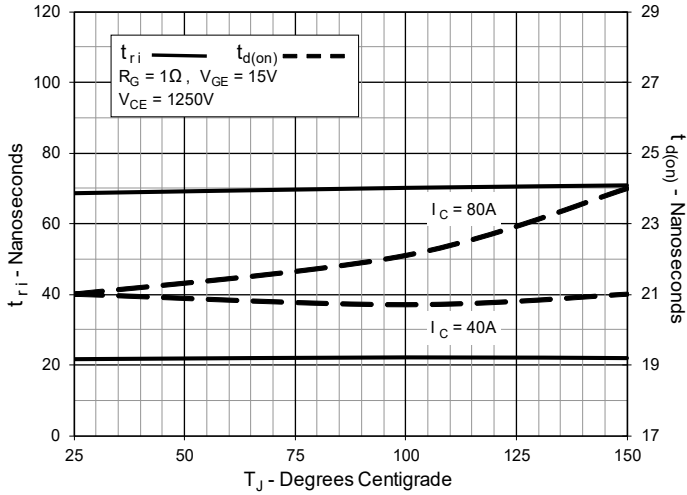
**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

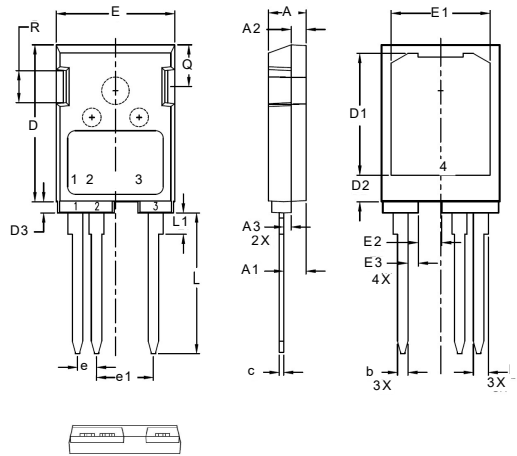


**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**



**TO-247PLUS-HV Outline**


**1 - Gate**  
**2,4 - Emitter**  
**3 - Collector**

SYM	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.193	0.201	4.90	5.10
A1	0.114	0.122	2.90	3.10
A2	0.075	0.083	1.90	2.10
A3	0.035	0.043	0.90	1.10
b	0.053	0.059	1.35	1.50
b1	0.075	0.083	1.90	2.10
c	0.022	0.030	0.55	0.75
D	0.819	0.843	20.8	21.4
D1	0.638	0.646	16.2	16.4
D2	0.134	0.146	3.40	3.70
D3	0.055	0.063	1.40	1.60
E	0.622	0.638	15.8	16.2
E1	0.520	0.528	13.2	13.4
E2	0.118	0.126	3.00	3.20
E3	0.051	0.059	1.30	1.50
e	0.100	BSC	2.54	BSC
e1	0.300	BSC	7.62	BSC
L	0.732	0.748	18.60	19.0
L1	0.106	0.118	2.70	3.00
Q	0.216	0.224	5.50	5.70
R	0.165	0.169	4.20	4.30